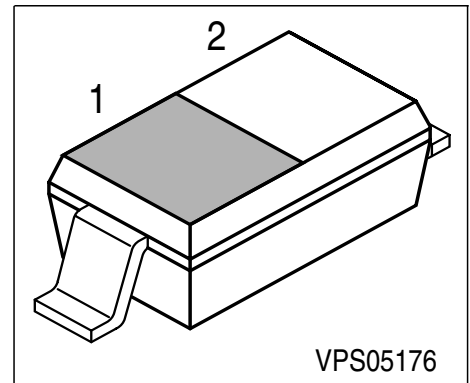


**Silicon Tuning Diode**

- High Q hyperabrupt dual tuning diode
- Designed for low tuning voltage operation
- For VCO's in mobile communications equipment



Type	Marking	Pin Configuration		Package
BBY 52-03W	I (white)	1 = C	2 = A	SOD-323

**Maximum Ratings**

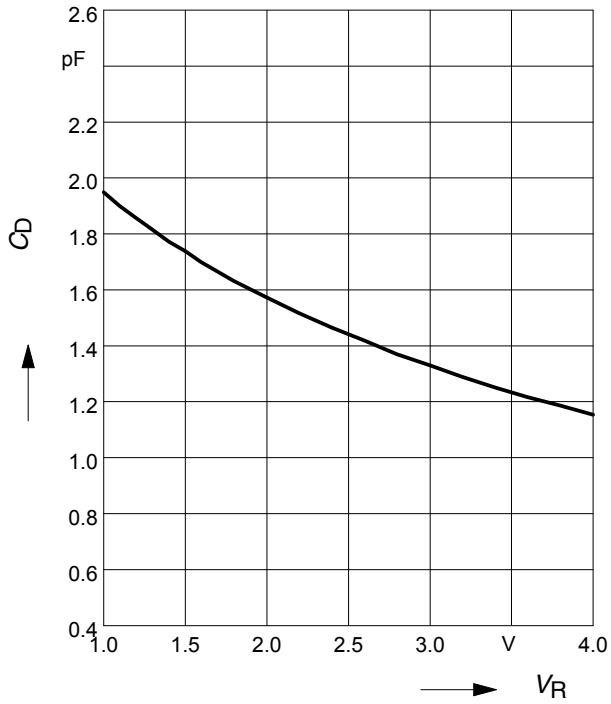
Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	7	V
Forward current	$I_F$	20	mA
Operating temperature range	$T_{op}$	-55 ... 150	°C
Storage temperature	$T_{stg}$	-55 ... 150	

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC characteristics</b>					
Reverse current $V_R = 6\text{ V}$	$I_R$	-	-	10	nA
Reverse current $V_R = 6\text{ V}, T_A = 150^\circ\text{C}$	$I_R$	-	-	100	
<b>AC characteristics</b>					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 2\text{ V}, f = 1\text{ MHz}$ $V_R = 3\text{ V}, f = 1\text{ MHz}$ $V_R = 4\text{ V}, f = 1\text{ MHz}$	$C_T$	1.4 0.95 0.9 0.85	1.85 1.5 1.35 1.15	2.2 2 1.75 1.45	pF
Capacitance ratio $V_R = 1\text{ V}, V_R = 4\text{ V}, f = 1\text{ MHz}$	$C_{T1}/C_{T4}$	1.1	1.6	2.1	-
Series resistance $V_R = 1\text{ V}, f = 1\text{ GHz}$	$r_s$	-	0.9	1.7	$\Omega$
Case capacitance $f = 1\text{ MHz}$	$C_C$	-	0.12	-	pF
Series inductance	$L_s$	-	1.8	-	nH

**Diode capacitance  $C_T = f(V_R)$**

$f = 1\text{MHz}$



**Reverse current  $I_R = f(V_R)$**

$T_A = 25\text{ }^\circ\text{C}$

